

# Eric Feltin

## List of Publications by Year in descending order

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16  
papers

1,046  
citations

687363

13  
h-index

996975

15  
g-index

16  
all docs

16  
docs citations

16  
times ranked

1128  
citing authors

#	ARTICLE	IF	CITATIONS
1	Room temperature polariton lasing in a GaN <sup>+</sup> /AlGa <sup>n</sup> multiple quantum well microcavity. Applied Physics Letters, 2008, 93, .	3.3	267
2	Stress control in GaN grown on silicon (111) by metalorganic vapor phase epitaxy. Applied Physics Letters, 2001, 79, 3230-3232.	3.3	258
3	205-GHz (Al,In)N/GaN HEMTs. IEEE Electron Device Letters, 2010, 31, 957-959.	3.9	132
4	Technology and Performance of InAlN/AlN/GaN HEMTs With Gate Insulation and Current Collapse Suppression Using Zr $\text{O}_2$ or Hf $\text{O}_2$ . IEEE Transactions on Electron Devices, 2008, 55, 937-941.	3.0	86
5	Large vacuum Rabi splitting in a multiple quantum well GaN-based microcavity in the strong-coupling regime. Physical Review B, 2008, 77, .	3.2	76
6	102-GHz AlInN/GaN HEMTs on Silicon With 2.5-W/mm Output Power at 10 GHz. IEEE Electron Device Letters, 2009, 30, 796-798.	3.9	49
7	Ultrahigh-Speed AlInN/GaN High Electron Mobility Transistors Grown on (111) High-Resistivity Silicon with $f_T = 143$ GHz. Applied Physics Express, 2010, 3, 094101.	2.4	37
8	Proposal and Performance Analysis of Normally Off $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{InAlN}/\text{AlN}/\text{GaN}$ HEMTs With 1-nm-Thick InAlN Barrier. IEEE Transactions on Electron Devices, 2010, 57, 2144-2154.	3.0	31
9	100-nm-Gate (Al,In)N/GaN HEMTs Grown on SiC With $f_T = 144$ GHz. IEEE Electron Device Letters, 2010, 31, 293-295.	3.9	30
10	Hexagonal c-axis GaN layers grown by metalorganic vapor-phase epitaxy on Si(001). Journal of Crystal Growth, 2005, 280, 44-53.	1.5	21
11	Biexciton kinetics in GaN quantum wells: Time-resolved and time-integrated photoluminescence measurements. Physical Review B, 2008, 77, .	3.2	16
12	Low-Noise Microwave Performance of 0.1 $\mu\text{m}$ Gate AlInN/GaN HEMTs on SiC. IEEE Microwave and Wireless Components Letters, 2010, 20, 453-455.	3.2	16
13	High reflectivity airgap distributed Bragg reflectors realized by wet etching of AlInN sacrificial layers. Applied Physics Letters, 2009, 95, .	3.3	13
14	Tailoring the strong coupling regime in III-nitride based microcavities for room temperature polariton laser applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2820-2827.	0.8	7
15	High-speed and low-noise AlInN/GaN HEMTs on SiC. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 429-433.	1.8	7
16	Progresses in III-Nitride Distributed Bragg Reflectors and Microcavities Using AlInN/GaN Materials. , 0, 261-286.		0